Supplementary Information

Experimental Conditions

Precursors :	In : TE In –Tri Ethyl Indium Sn : TMT - Tetra Methyl Tin
Shower head temperature	325 ^{o}C
Surface temperature	250^{o}C
substrate	Si
Working pressure :	0.3 Torr.
Ar : O	100 :10
Dep. Time	1 Hr.

Elements	Binding energy (eV)
In 3d $_{3/2}$	**452.505 eV**
In 3d $_{5/2}$	**444.905 eV**
O 1s	**530.6 eV**

Table 1. (a) Experimental condition (b) values of Binding energies of In and Oxygen from XPS analysis

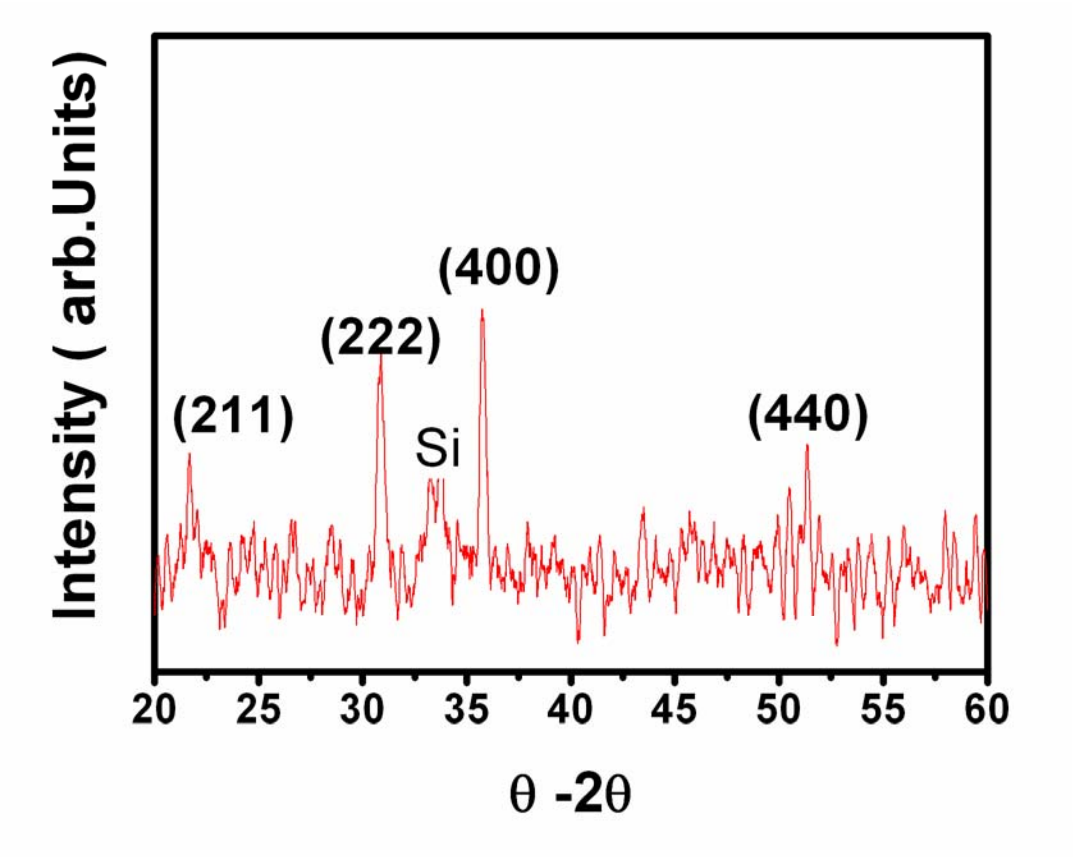
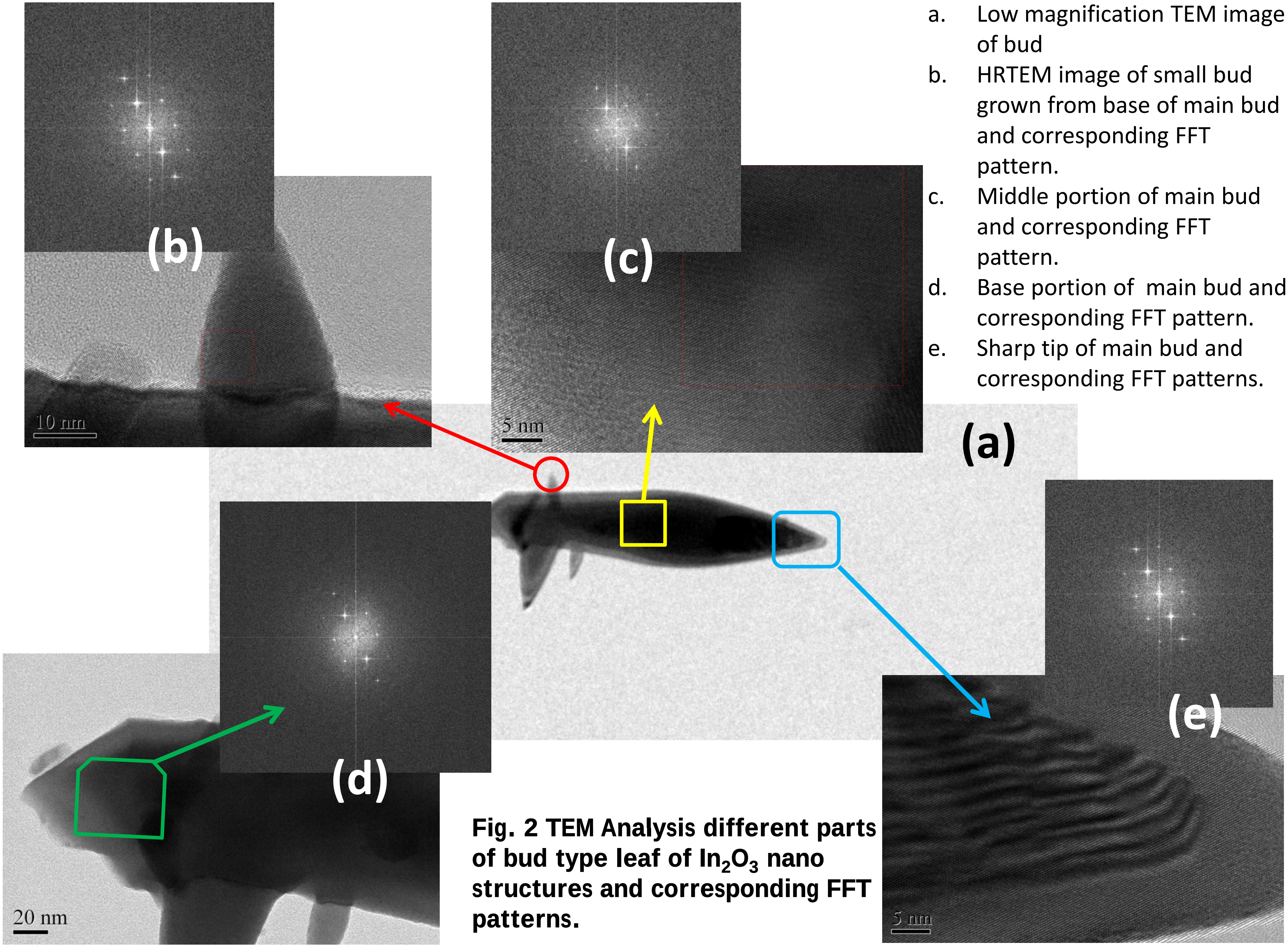


Fig.1 XRD patterns of In_2O_3 flower like structures grown on Si substrate.



a. Low magnification TEM image of bud
b. HRTEM image of small bud grown from base of main bud and corresponding FFT pattern.
c. Middle portion of main bud and corresponding FFT pattern.
d. Base portion of main bud and corresponding FFT pattern.
e. Sharp tip of main bud and corresponding FFT patterns.

Fig. 2 TEM Analysis different parts of bud type leaf of In_2O_3 nano structures and corresponding FFT patterns.

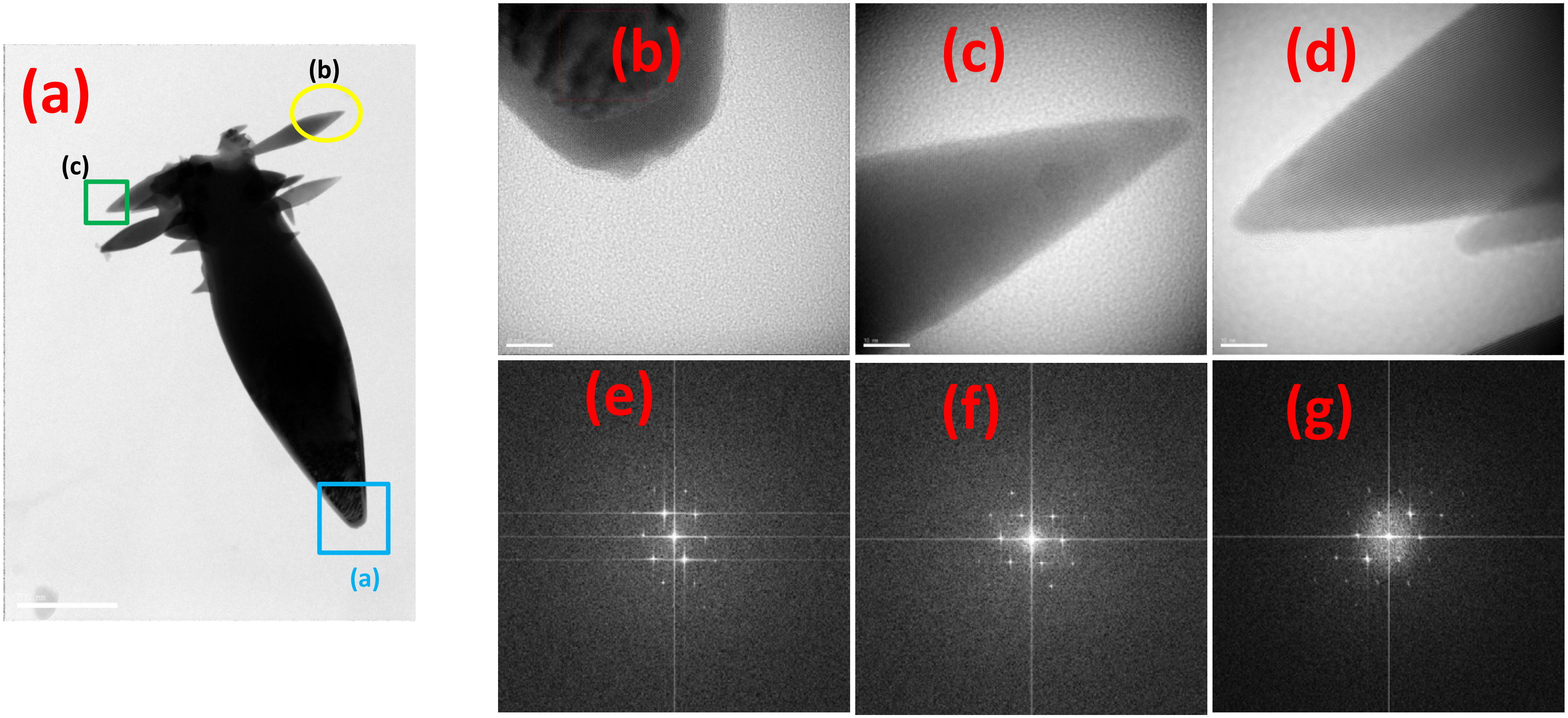


Fig. 3 (a) Low magnification TEM image of bud type leaf of In_2O_3 nano structures (b) (c) and(d) are HRTEM images of tips parts of different buds and (e) (f) and (g) are corresponding FFT patterns respectively.